## **ELECTRONIC INFORMATION DISCLOSURE STATEMENT**

Electronic Version v18

Stylesheet Version v18.0

Title of Invention

GATE ELECTRODE FORMING METHODS USING CONDUCTIVE HARD MASK

**Application Number:** 

Confirmation Number:

First Named Applicant:

Oleg Gluschenkov

**Attorney Docket Number:** 

FIS920040196US1

Art Unit:

Examiner:

Search string:

(6693333 or 6664153 or 6633497 or 6448590 or 6441447 or 6426301 or 6204073

or 20030109121 or 20030153139 or 20020196647 or 20020177279 or

20030104663 ).pn

## **US Patent Documents**

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

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## **US Published Applications**

Note: Applicant is not required to submit a paper copy of cited US Published Applications

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